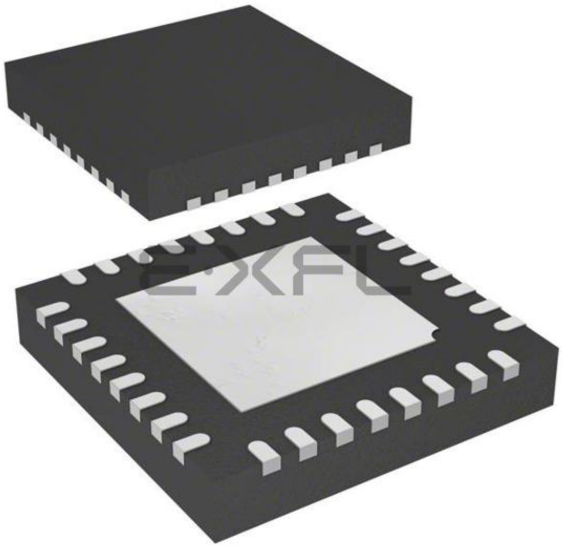

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	24
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 8x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-UFQFN Exposed Pad
Supplier Device Package	32-UFQFPN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f302k8u7

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List of figures

Table 10. No. of capacitive sensing channels available on STM32F302x6/8 devices (continued)

Analog I/O group	Number of capacitive sensing channels		
	STM32F302Rx	STM32F302Cx	STM32F302Kx
G6	3	3	0
Number of capacitive sensing channels	18	17	13

3.23 Infrared transmitter

The STM32F302x6/8 devices provide an infrared transmitter solution. The solution is based on internal connections between TIM16 and TIM17 as shown in the figure below.

TIM17 is used to provide the carrier frequency and TIM16 provides the main signal to be sent. The infrared output signal is available on PB9 or PA13.

To generate the infrared remote control signals, TIM16 channel 1 and TIM17 channel 1 must be properly configured to generate correct waveforms. All standard IR pulse modulation modes can be obtained by programming the two timers output compare channels.

Figure 3. Infrared transmitter

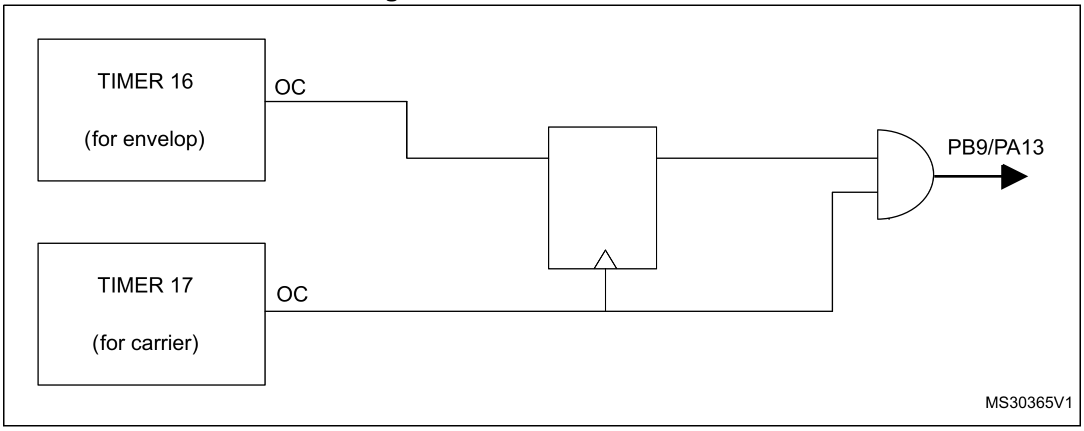
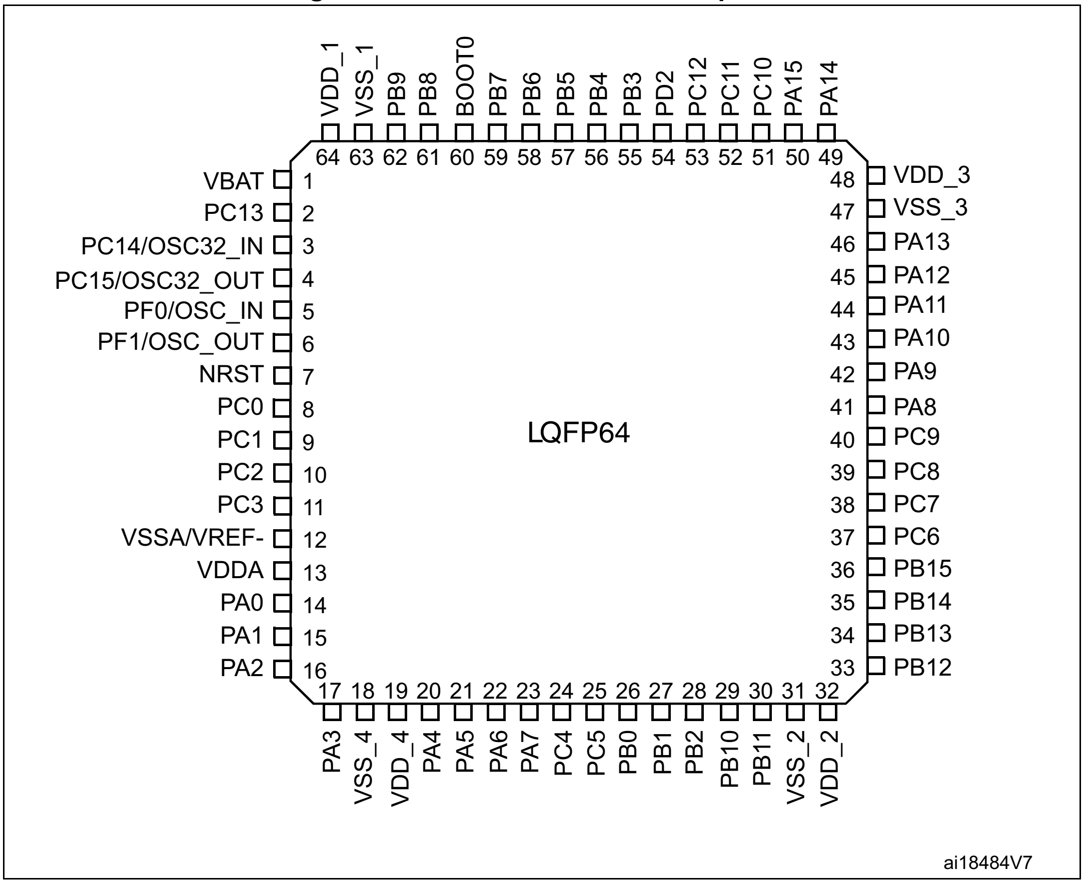


Figure 6. STM32F302x6/8 LQFP64 pinout



1. The above figure shows the package top view.

Table 12. STM32F302x6/8 pin definitions

Pin Number				Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN32	WLCSP49	LQFP48	LQFP64						
-	B6	1	1	VBAT	S	-	-	Backup power supply	
-	D5	2	2	PC13(1) TAMPER1 WKUP2 (PC13)	I/O	TC	(1)	TIM1_CH1N	WKUP2, RTC_TAMP1, RTC_TS, RTC_OUT
-	C7	3	3	PC14(1) OSC32_IN (PC14)	I/O	TC	(1)	-	OSC32_IN
-	C6	4	4	PC15(1) OSC32_OUT (PC14)	I/O	TC	(1)	-	OSC32_OUT
2	D7	5	5	PF0 OSC_IN (PF0)	I/O	FTf	-	I2C2_SDA, SPI2_NSS/I2S2_WS, TIM1_CH3N	OSC_IN
3	D6	6	6	PF1 OSC_OUT (PF1)	O	FTf	-	I2C2_SCL, SPI2_SCK/I2S2_CK	OSC_OUT
4	E7	7	7	NRST	I/O	RST	-	Device reset input/internal reset output (active low)	
-	-	-	8	PC0	I/O	TTa	-	EVENTOUT, TIM1_CH1	ADC1_IN6
-	-	-	9	PC1	I/O	TTa	-	EVENTOUT, TIM1_CH2	ADC1_IN7
-	-	-	10	PC2	I/O	TTa	-	EVENTOUT, TIM1_CH3	ADC1_IN8
-	-	-	11	PC3	I/O	TTa	-	EVENTOUT, TIM1_CH4, TIM1_BKIN2	ADC1_IN9
6	E6	8	12	VSSA/VREF-	S	-	-	Analog ground/Negative reference voltage	
5	A6	9	13	VDDA/VREF+	S	-	-	Analog power supply/Positive reference voltage	

Table 12. STM32F302x6/8 pin definitions (continued)

Pin Number				Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN32	WLCSP49	LQFP48	LQFP64						
7	F6	10	14	PA0 -TAMPER2-WKUP1	I/O	TTa	(2)	TIM2_CH1/TIM2_ETR, TSC_G1_IO1, USART2_CTS, EVENTOUT	ADC1_IN1, RTC_TAMP2, WKUP1
8	G7	11	15	PA1	I/O	TTa	(2)	RTC_REFIN, TIM2_CH2, TSC_G1_IO2, USART2_RTS_DE, TIM15_CH1N, EVENTOUT	ADC1_IN2
9	E5	12	16	PA2	I/O	TTa	(2)	TIM2_CH3, TSC_G1_IO3, USART2_TX, COMP2_OUT, TIM15_CH1, EVENTOUT	ADC1_IN3, COMP2_INM
10	E4	13	17	PA3	I/O	TTa	(2)	TIM2_CH4, TSC_G1_IO4, USART2_RX, TIM15_CH2, EVENTOUT	ADC1_IN4
-	F7	-	18	VSS_4	S	-	-	-	-
-	F2	-	19	VDD_4	S	-	-	-	-
11	G6	14	20	PA4	I/O	TTa	(2)(3)	TSC_G2_IO1, SPI3_NSS/I2S3_WS, USART2_CK, EVENTOUT	ADC1_IN5, DAC1_OUT1, COMP2_INM, COMP4_INM, COMP6_INM
12	F5	15	21	PA5	I/O	TTa	-	TIM2_CH1/TIM2_ETR, TSC_G2_IO2, EVENTOUT	OPAMP2_VINM
13	F4	16	22	PA6	I/O	TTa	(3)	TIM16_CH1, TSC_G2_IO3, TIM1_BKIN, EVENTOUT	ADC1_IN10, OPAMP2_VOUT
14	F3	17	23	PA7	I/O	TTa	-	TIM17_CH1, TSC_G2_IO4, TIM1_CH1N, EVENTOUT	ADC1_IN15, COMP2_INP, OPAMP2_VINP

Table 12. STM32F302x6/8 pin definitions (continued)

Pin Number				Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN32	WLCSP49	LQFP48	LQFP64						
-	-	-	24	PC4	I/O	TT	-	EVENTOUT, TIM1_ETR, USART1_TX	
-	-	-	25	PC5	I/O	TTa	-	EVENTOUT, TIM15_BKIN, TSC_G3_IO1, USART1_RX	OPAMP2_VINM
15	G5	18	26	PB0	I/O	TTa	-	TSC_G3_IO2, TIM1_CH2N, EVENTOUT	ADC1_IN11, COMP4_INP, OPAMP2_VINP
-	G4	19	27	PB1	I/O	TTa	-	TSC_G3_IO3, TIM1_CH3N, COMP4_OUT, EVENTOUT	ADC1_IN12
-	G3	20	28	PB2	I/O	TTa	-	TSC_G3_IO4, EVENTOUT	COMP4_INM
-	E3	21	29	PB10	I/O	TT	-	TIM2_CH3, TSC_SYNC, USART3_TX, EVENTOUT	
-	G2	22	30	PB11	I/O	TTa	-	TIM2_CH4, TSC_G6_IO1, USART3_RX, EVENTOUT	ADC1_IN14, COMP6_INP
16	D3	23	31	VSS_2	S	-	-	Digital ground	
17	B2	24	32	VDD_2	S	-	-	Digital power supply	
-	E2	25	33	PB12	I/O	TT	-	TSC_G6_IO2, I2C2_SMBAL, SPI2_NSS/I2S2_WS, TIM1_BKIN, USART3_CK, EVENTOUT	
-	G1	26	34	PB13	I/O	TTa	-	TSC_G6_IO3, SPI2_SCK/I2S2_CK, TIM1_CH1N, USART3_CTS, EVENTOUT	ADC1_IN13

Table 12. STM32F302x6/8 pin definitions (continued)

Pin Number				Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN32	WLCSP49	LQFP48	LQFP64						
31	A5	44	60	BOOT0	I	B	-	Boot memory selection	
-	B5	45	61	PB8	I/O	FTf	-	TIM16_CH1, TSC_SYNC, I2C1_SCL, USART3_RX, CAN_RX, TIM1_BKIN, EVENTOUT	-
-	C5	46	62	PB9	I/O	FTf	-	TIM17_CH1, I2C1_SDA, IR-OUT, USART3_TX, COMP2_OUT, CAN_TX, EVENTOUT	-
32	D3	47	63	VSS_1	S	-	-	Digital ground	
"1"	B7	48	64	VDD_1	S	-	-	Digital power supply	

1. PC13, PC14 and PC15 are supplied through the power switch. Since the switch sinks only a limited amount of current (3 mA), the use of GPIO PC13 to PC15 in output mode is limited:

   - The speed should not exceed 2 MHz with a maximum load of 30 pF

   - These GPIOs must not be used as current sources (e.g. to drive an LED).

   After the first backup domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the Backup registers which is not reset by the main reset. For details on how to manage these GPIOs, refer to the Battery backup domain and BKP register description sections in the RM0365 reference manual.
2. Fast ADC channel.
3. These GPIOs offer a reduced touch sensing sensitivity. It is thus recommended to use them as sampling capacitor I/O.

Table 14. Alternate functions for Port B (continued)

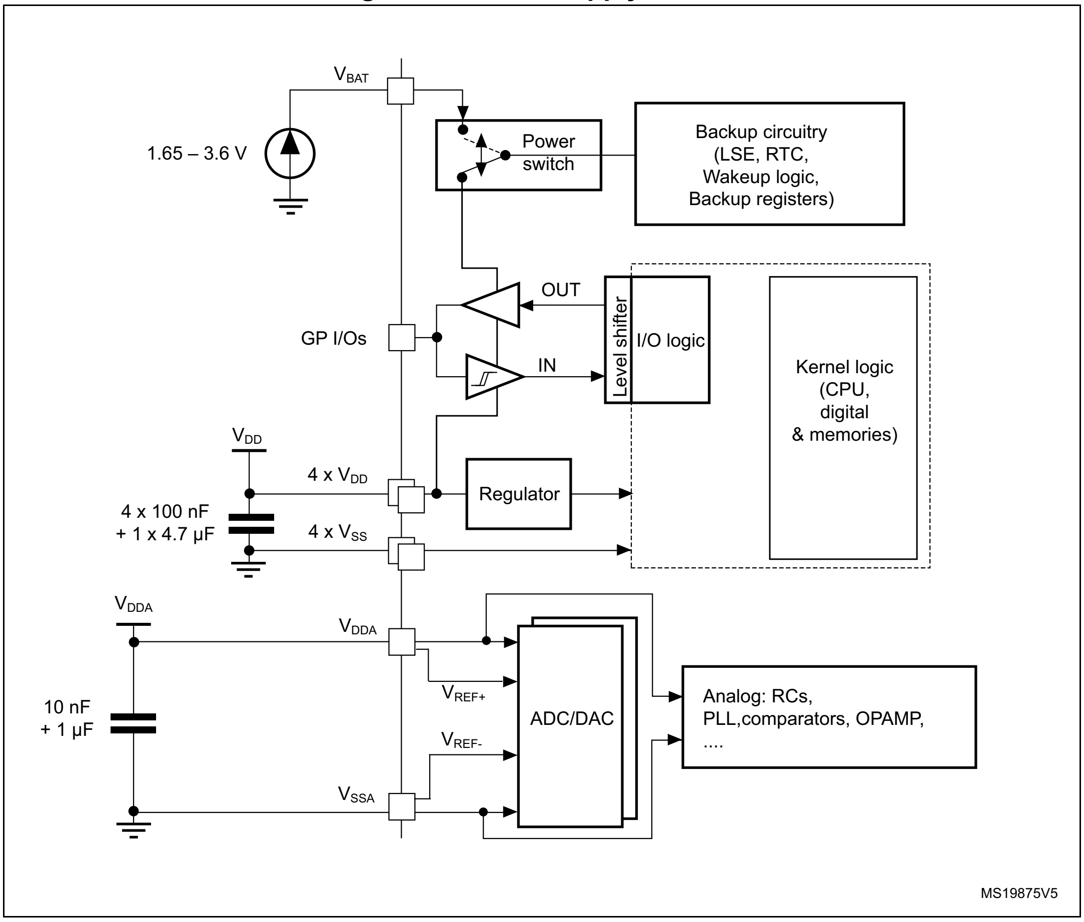
Port & pin name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
	SYS_AF	TIM2/TIM15/TIM16 /TIM17/EVENT	I2C3/TIM1/TIM2/TIM15	I2C3/TIM15/TSC	I2C1/I2C2/TIM1/ TIM16/TIM17	SPI2/I2S2/ SPI3/I2S3/Infrared	SPI2/I2S2/SPI3/ I2S3/TIM1/Infrared	USART1/USART2/USART3/ CAN/GPCOMP6	I2C3/GPCOMP2 /GPCOMP4/GPCOMP6	CAN/TIM1/TIM15	TIM2/TIM17	TIM1	TIM1	-	-	EVENT
PB9	-	TIM17 _CH1	-	-	I2C1 _SDA	-	IR-OUT	USART3 _TX	COMP2_ OUT	CAN _TX	-	-	-	-	-	EVENT OUT
PB10	-	TIM2 _CH3	-	TSC _SYNC	-	-	-	USART3 _TX	-	-	-	-	-	-	-	EVENT OUT
PB11	-	TIM2 _CH4	-	TSC _G6_IO1	-	-	-	USART3 _RX	-	-	-	-	-	-	-	EVENT OUT
PB12	-	-	-	TSC _G6_IO2	I2C2 _SMBAL	SPI2_NS S/I2S2_ WS	TIM1 _BKIN	USART3 _CK	-	-	-	-	-	-	-	EVENT OUT
PB13	-	-	-	TSC _G6_IO3	-	SPI2_SC K/ I2S2_CK	TIM1 _CH1N	USART3 _CTS	-	-	-	-	-	-	-	EVENT OUT
PB14	-	TIM15 _CH1	-	TSC _G6_IO4	-	SPI2_MI SO/I2S2 ext_SD	TIM1 _CH2N	USART3 _RTS _DE	-	-	-	-	-	-	-	EVENT OUT
PB15	RTC _REFIN	TIM15 _CH2	TIM15 _CH1N	-	TIM1 _CH3N	SPI2_M OSI/ I2S2_SD	-	-	-	-	-	-	-	-	-	EVENT OUT

Table 18. STM32F302x6 STM32F302x8 peripheral register boundary addresses (continued)[1]

Bus	Boundary address	Size (bytes)	Peripheral
APB1	0x4000 7800 - 0x4000 7BFF	9 K	I2C3
	0x4000 7400 - 0x4000 77FF	1 K	DAC1
	0x4000 7000 - 0x4000 73FF	1 K	PWR
	0x4000 6C00 - 0x4000 6FFF	1 K	Reserved
	0x4000 6800 - 0x4000 6BFF	1 K	Reserved
	0x4000 6400 - 0x4000 67FF	1 K	bxCAN
	0x4000 6000 - 0x4000 63FF	1 K	USB/CAN SRAM
	0x4000 5C00 - 0x4000 5FFF	1 K	USB device FS
	0x4000 5800 - 0x4000 5BFF	1 K	I2C2
	0x4000 5400 - 0x4000 57FF	1 K	I2C1
	0x4000 5000 - 0x4000 53FF	1 K	Reserved
	0x4000 4C00 - 0x4000 4FFF	1 K	Reserved
	0x4000 4800 - 0x4000 4BFF	1 K	USART3
	0x4000 4400 - 0x4000 47FF	1 K	USART2
	0x4000 4000 - 0x4000 43FF	1 K	I2S3ext
	0x4000 3C00 - 0x4000 3FFF	1 K	SPI3/I2S3
	0x4000 3800 - 0x4000 3BFF	1 K	SPI2/I2S2
	0x4000 3400 - 0x4000 37FF	1 K	I2S2ext
	0x4000 3000 - 0x4000 33FF	1 K	IWDG
	0x4000 2C00 - 0x4000 2FFF	1 K	WWDG
	0x4000 2800 - 0x4000 2BFF	1 K	RTC
	0x4000 1400 - 0x4000 27FF	5 K	Reserved
	0x4000 1000 - 0x4000 13FF	1 K	TIM6
	0x4000 0C00 - 0x4000 0FFF	1 K	Reserved
	0x4000 0800 - 0x4000 0BFF	1 K	Reserved
	0x4000 0400 - 0x4000 07FF	1 K	Reserved
	0x4000 0000 - 0x4000 03FF	1 K	TIM2
	0x2000 A000 - 3FFF FFFF	~512 M	Reserved
	0x2000 0000 - 0x2000 9FFF	40 K	SRAM
	0x1FFF F800 - 0x1FFF FFFF	2 K	Option bytes
	0x1FFF D800 - 0x1FFF F7FF	8 K	System memory
	0x0804 0000 - 0x1FFF D7FF	~384 M	Reserved
	0x0800 0000 - 0x0800 FFFF	64 K	Main Flash memory

6.1.6 Power supply scheme

Figure 11. Power supply scheme



Caution: Each power supply pair (for example V_{DD}/V_{SS}, V_{DDA}/V_{SSA}) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 53: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see *Table 36: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_S$

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 41*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 41. HSE oscillator characteristics

Symbol	Parameter	Conditions(1)	Min(2)	Typ	Max(2)	Unit
f_{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
I_{DD}	HSE current consumption	During startup(3)	-	-	8.5	mA
		V_{DD}=3.3 V, Rm= 30Ω, CL=10 pF@8 MHz	-	0.4	-	
		V_{DD}=3.3 V, Rm= 45Ω, CL=10 pF@8 MHz	-	0.5	-	
		V_{DD}=3.3 V, Rm= 30Ω, CL= 5 pF@32 MHz	-	0.8	-	
		V_{DD}=3.3 V, Rm= 30Ω, CL=10 pF@32 MHz	-	1	-	
		V_{DD}=3.3 V, Rm= 30Ω, CL=20 pF@32 MHz	-	1.5	-	
g_m	Oscillator transconductance	Startup	10	-	-	mA/V
$t_{SU(HSE)}$(4)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by design.
3. This consumption level occurs during the first 2/3 of the $t_{SU(HSE)}$ startup time.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

6.3.10 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

Table 46. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max(1)	Unit
t_{prog}	16-bit programming time	T_A = –40 to +105 °C	40	53.5	60	µs
t_{ERASE}	Page (2 KB) erase time	T_A = –40 to +105 °C	20	-	40	ms
t_{ME}	Mass erase time	T_A = –40 to +105 °C	20	-	40	ms
I_{DD}	Supply current	Write mode	-	-	10	mA
		Erase mode	-	-	12	mA

1. Guaranteed by design.

Table 47. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value Min(1)	Unit
N_{END}	Endurance	T_A = –40 to +85 °C (6 suffix versions) T_A = –40 to +105 °C (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	10	
		10 kcycles(2) at T_A = 55 °C	20	

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 23* and *Table 55*, respectively.

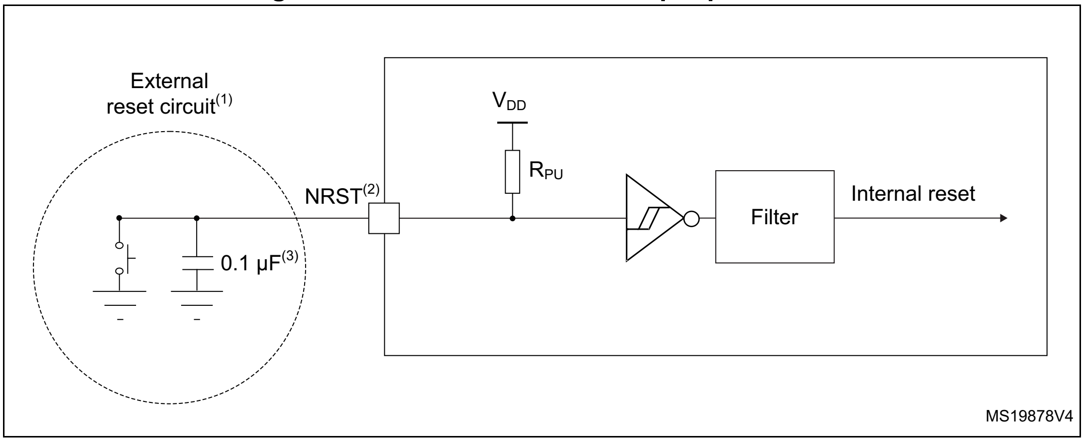
Unless otherwise specified, the parameters given are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 22*.

Table 55. I/O AC characteristics[(1)]

OSPEEDRy [1:0] value[(1)]	Symbol	Parameter	Conditions	Min	Max	Unit
x0	$f_{max(IO)out}$	Maximum frequency[(2)]	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	-	2[(3)]	MHz
	$t_{f(IO)out}$	Output high to low level fall time	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	-	125[(3)]	ns
	$t_{r(IO)out}$	Output low to high level rise time		-	125[(3)]	
01	$f_{max(IO)out}$	Maximum frequency[(2)]	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	-	10[(3)]	MHz
	$t_{f(IO)out}$	Output high to low level fall time	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	-	25[(3)]	ns
	$t_{r(IO)out}$	Output low to high level rise time		-	25[(3)]	
11	$f_{max(IO)out}$	Maximum frequency[(2)]	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	50[(3)]	MHz
			C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	30[(3)]	MHz
			C_L = 50 pF, V_{DD} = 2 V to 2.7 V	-	20[(3)]	MHz
	$t_{f(IO)out}$	Output high to low level fall time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	5[(3)]	ns
			C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	8[(3)]	
			C_L = 50 pF, V_{DD} = 2 V to 2.7 V	-	12[(3)]	
	$t_{r(IO)out}$	Output low to high level rise time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	5[(3)]	
			C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	8[(3)]	
			C_L = 50 pF, V_{DD} = 2 V to 2.7 V	-	12[(3)]	
FM+ configuration[(4)]	$f_{max(IO)out}$	Maximum frequency[(2)]	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	-	2[(4)]	MHz
	$t_{f(IO)out}$	Output high to low level fall time		-	12[(4)]	ns
	$t_{r(IO)out}$	Output low to high level rise time		-	34[(4)]	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	10	-‘	ns

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the RM0365 reference manual for a description of GPIO Port configuration register.
2. The maximum frequency is defined in *Figure 23*.
3. Guaranteed by design.
4. The I/O speed configuration is bypassed in FM+ I/O mode. Refer to the STM32F302x6 STM32F302x8 reference manual RM0365 for a description of FM+ I/O mode configuration.

Figure 24. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 56*. Otherwise the reset will not be taken into account by the device.
3. The user must place the external capacitor on NRST as close as possible to the chip.

6.3.16 Timer characteristics

The parameters given in *Table 57* are guaranteed by design.

Refer to *Section 6.3.14: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 57. TIMx[(1)(2)] characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	-	1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 72 MHz	13.9	-	ns
		$f_{TIMxCLK}$ = 144 MHz, x = 1, 15,16, 17	6.95	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	-	0	$f_{TIMxCLK}/2$	MHz
		$f_{TIMxCLK}$ = 72 MHz	0	36	MHz
Res_{TIM}	Timer resolution	TIMx (except TIM2)	-	16	bit
		TIM2	-	32	
$t_{COUNTER}$	16-bit counter clock period	-	1	65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 72 MHz	0.0139	910	µs
		$f_{TIMxCLK}$ = 144 MHz, x= 1/15/16/17	0.0069	455	µs
t_{MAX_COUNT}	Maximum possible count with 32-bit counter	-	-	65536 × 65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 72 MHz	-	59.65	s
		$f_{TIMxCLK}$ = 144 MHz, x= 1/15/16/17	-	29.825	s

1. TIMx is used as a general term to refer to the TIM1, TIM2, TIM15, TIM16 and TIM17 timers.
2. Guaranteed by design.

Table 65. USB: Full-speed electrical characteristics[1] (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	-	110	%
V_{CRS}	Output signal crossover voltage		1.3	-	2.0	V
Output driver Impedance[3]	Z_{DRV}	driving high and low	28	40	44	Ω

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).
3. No external termination series resistors are required on USB_DP (D+) and USB_DM (D-), the matching impedance is already included in the embedded driver.

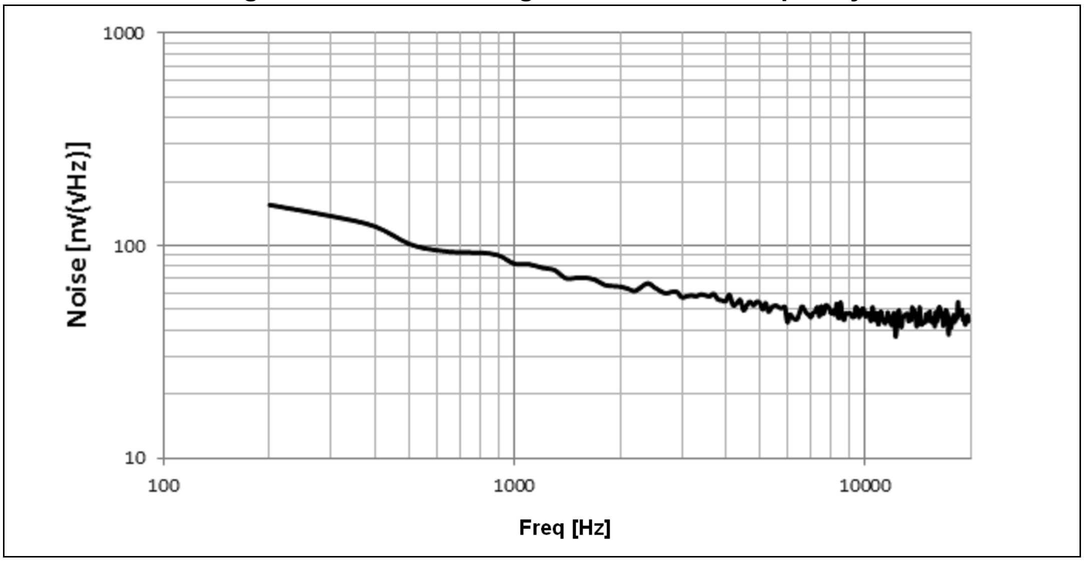
CAN (controller area network) interface

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (CAN_TX and CAN_RX).

Table 68. ADC accuracy - limited test conditions(1)(2)

Symbol	Parameter	Conditions			Min (3)	Typ	Max (3)	Unit
ET	Total unadjusted error	ADC clock freq. ≤ 72 MHz Sampling freq. ≤ 5 Msps V_{DDA} = 3.3 V 25°C	Single ended	Fast channel 5.1 Ms	-	±4	±4.5	LSB
				Slow channel 4.8 Ms	-	±5.5	±6	
			Differential	Fast channel 5.1 Ms	-	±3.5	±4	
				Slow channel 4.8 Ms	-	±3.5	±4	
EO	Offset error		Single ended	Fast channel 5.1 Ms	-	±2	±2	
				Slow channel 4.8 Ms	-	±1.5	±2	
			Differential	Fast channel 5.1 Ms	-	±1.5	±2	
				Slow channel 4.8 Ms	-	±1.5	±2	
EG	Gain error		Single ended	Fast channel 5.1 Ms	-	±3	±4	
				Slow channel 4.8 Ms	-	±5	±5.5	
			Differential	Fast channel 5.1 Ms	-	±3	±3	
				Slow channel 4.8 Ms	-	±3	±3.5	
ED	Differential linearity error		Single ended	Fast channel 5.1 Ms	-	±1	±1	
				Slow channel 4.8 Ms	-	±1	±1	
			Differential	Fast channel 5.1 Ms	-	±1	±1	
				Slow channel 4.8 Ms	-	±1	±1	
EL	Integral linearity error		Single ended	Fast channel 5.1 Ms	-	±1.5	±2	
				Slow channel 4.8 Ms	-	±2	±3	
			Differential	Fast channel 5.1 Ms	-	±1.5	±1.5	
				Slow channel 4.8 Ms	-	±1.5	±2	
ENOB (4)	Effective number of bits		Single ended	Fast channel 5.1 Ms	10.8	10.8	-	bit
				Slow channel 4.8 Ms	10.8	10.8	-	
			Differential	Fast channel 5.1 Ms	11.2	11.3	-	
				Slow channel 4.8 Ms	11.2	11.3	-	
SINAD (4)	Signal-to-noise and distortion ratio		Single ended	Fast channel 5.1 Ms	66	67	-	dB
				Slow channel 4.8 Ms	66	67	-	
			Differential	Fast channel 5.1 Ms	69	70	-	
				Slow channel 4.8 Ms	69	70	-	

Figure 36. OPAMP Voltage Noise versus Frequency

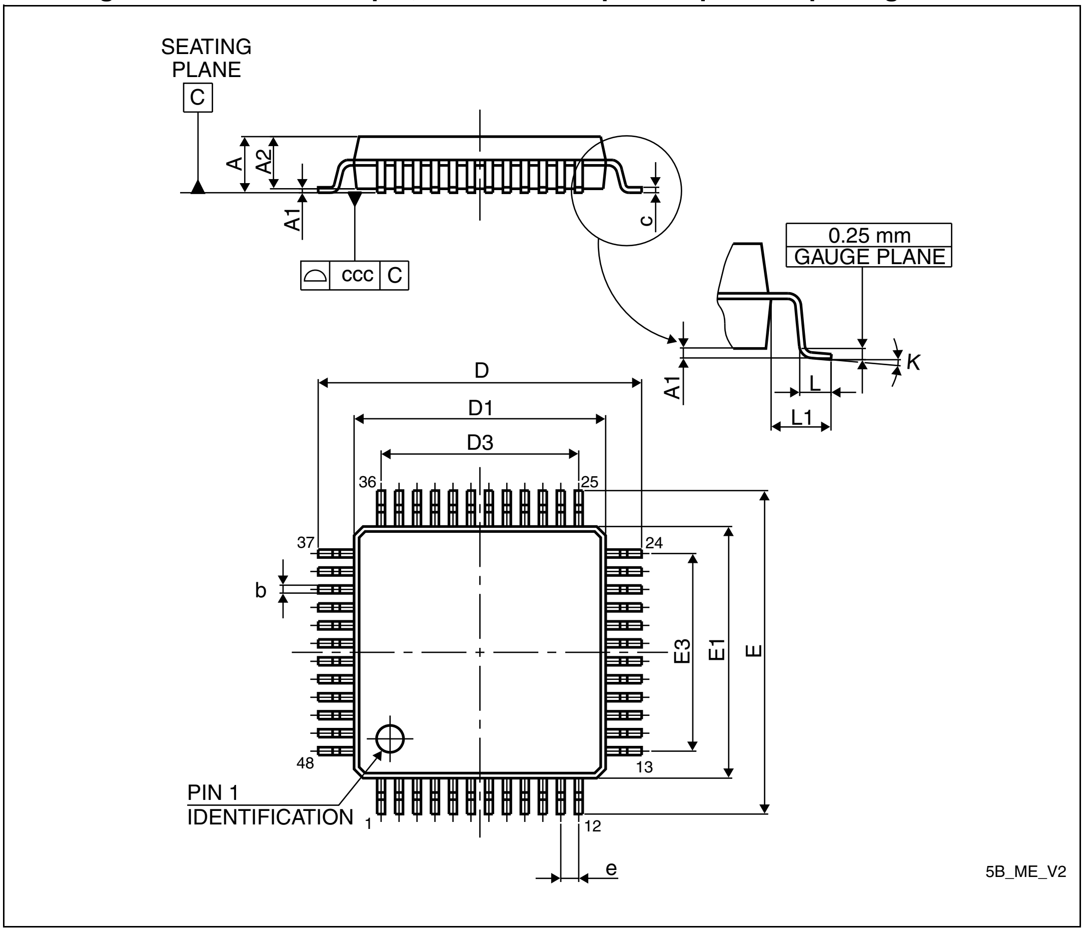


7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

7.3 LQFP48 package information

Figure 43. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



1. Drawing is not to scale.